June 2017

SemiHow
Know-How for Semiconductor

HRW120N10K

100V N-Channel Trench MOSFET

Features

- ❑ Low Dense Cell Design
- ❑ Reliable and Rugged
- ❑ Advanced Trench Process Technology
- ❑ 100% UIS Tested, 100% Rg Tested
- ❑ Lead free, Halogen Free

Application

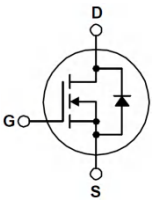
- ❑ Power Management in Inverter System
- ❑ Synchronous Rectification

Key Parameters

Parameter	Value	Unit
BV_{DSS}	100	V
I_D	73	A
$R_{DS(on),\ typ}$	10	mΩ

Package & Internal Circuit

D^2-PAK



Absolute Maximum Ratings

T_J=25℃ unless otherwise specified

Symbol	Parameter		Value	Units
V_{DSS}	Drain-Source Voltage		100	V
V_{GS}	Gate-Source Voltage		±25	V
I_D	Drain Current (Silicon Limited)	T_C= 25℃	73	A
		T_C = 100℃	51	A
		T_A= 25℃	12	A
		T_A= 70℃	10	A
I_{DM}	Pulsed Drain Current		200	A
E_{AS}	Single Pulsed Avalanche Energy	L=1mH	265	mJ
P_D	Power Dissipation	T_A = 25℃	3.75	W
		T_C = 25℃	136	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.1	℃/W
$R_{\theta JA}$	Junction-to-Ambient (minimum pad of 2 oz copper)	--	62.5	℃/W
$R_{\theta JA}$	Junction-to-Ambient (* 1in^2 pad of 2 oz copper)	--	40	℃/W

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Electrical Characteristics T_J=25 °C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
On Characteristics						
V_{GS}	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	3.6	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 40 A	--	10	12	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 40 A	--	80	--	S
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	100	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 80 V, T_J = 125℃	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±25 V, V_{DS} = 0 V	--	--	±100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1.0 MHz	--	3000	--	pF
C_{oss}	Output Capacitance		--	250	--	pF
C_{rss}	Reverse Transfer Capacitance		--	135	--	pF
R_g	Gate Resistance	V_{GS} = 0 V, V_{DS} = 0 V, f = 1MHz	--	1.2	--	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 50 V, I_D = 30 A, R_G = 6 Ω	--	40	--	ns
t_r	Turn-On Rise Time		--	50	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	120	--	ns
t_f	Turn-Off Fall Time		--	40	--	ns
Q_g	Total Gate Charge	V_{DS} = 80 V, I_D = 30 A, V_{GS} = 10 V	--	65	85	nC
Q_{gs}	Gate-Source Charge		--	12	--	nC
Q_{gd}	Gate-Drain Charge		--	24	--	nC
Source-Drain Diode Characteristics						
I_S	Continuous Drain-Source Diode Forward Current		--	--	73	A
I_{SM}	Pulsed Drain-Source Diode Forward Current		--	--	200	A
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 30 A, V_{GS} = 0 V	--	--	1.3	V
trr	Reverse Recovery Time	I_S = 30 A, V_{GS} = 0 V, di_F/dt = 100 A/μs	--	50	--	ns
Qrr	Reverse Recovery Charge		--	80	--	nC

Notes :

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L=1mH, I_{AS}=17A, V_{DD}=25V, R_G=25Ω, Starting T_J=25°C

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Typical Characteristics

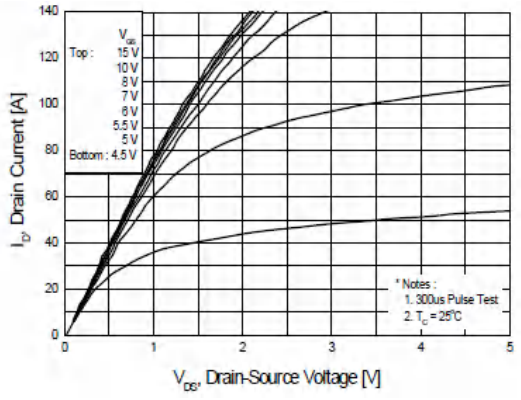

Figure 1. On Region Characteristics

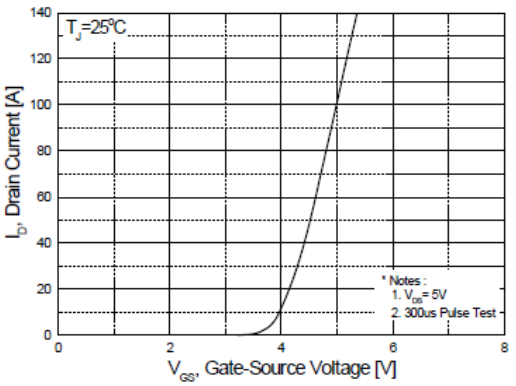

Figure 2. Transfer Characteristics

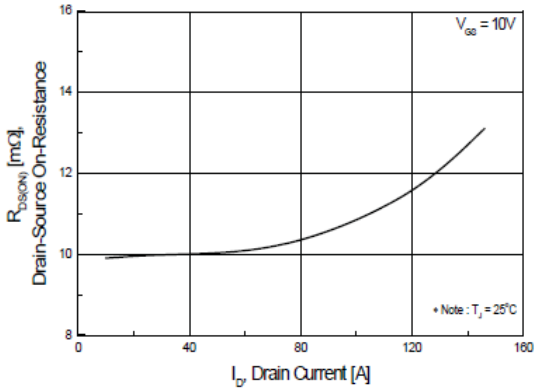

Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

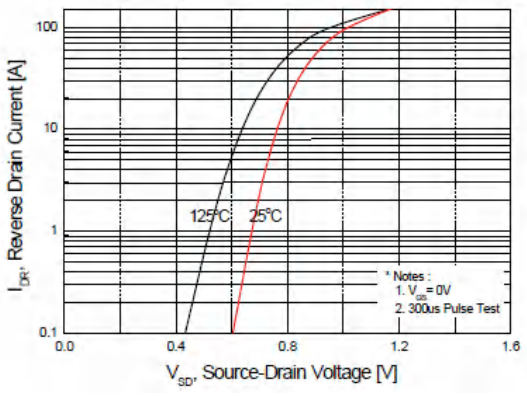

Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

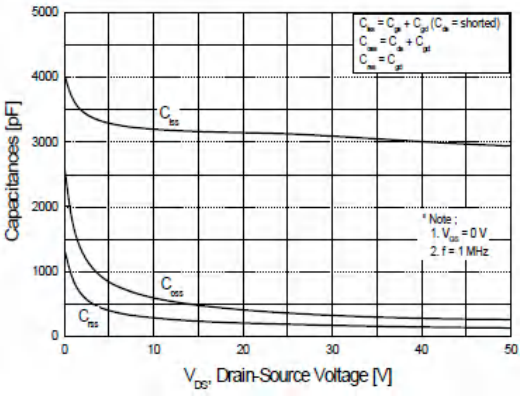

Figure 5. Capacitance Characteristics

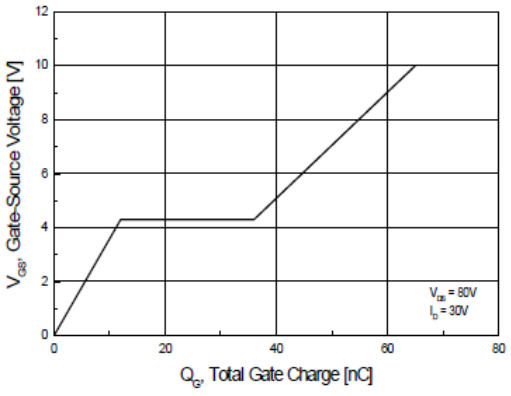

Figure 6. Gate Charge Characteristics

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Typical Characteristics (continued)

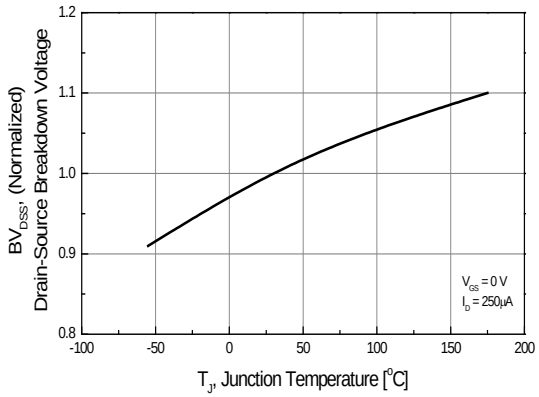

Figure 7. Breakdown Voltage Variation vs Temperature

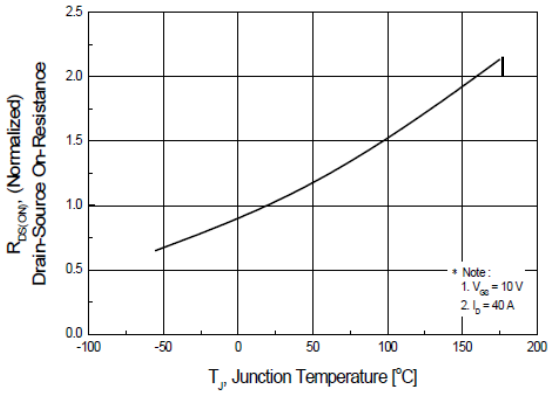

Figure 8. On-Resistance Variation vs Temperature

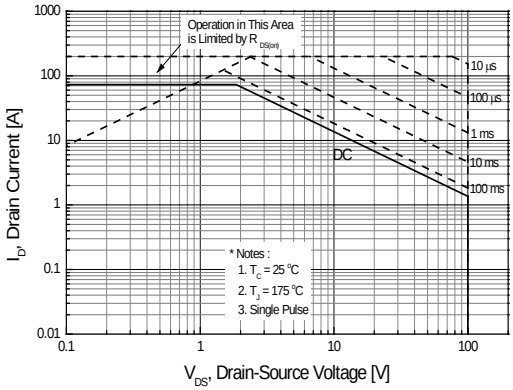

Figure 9. Maximum Safe Operating Area

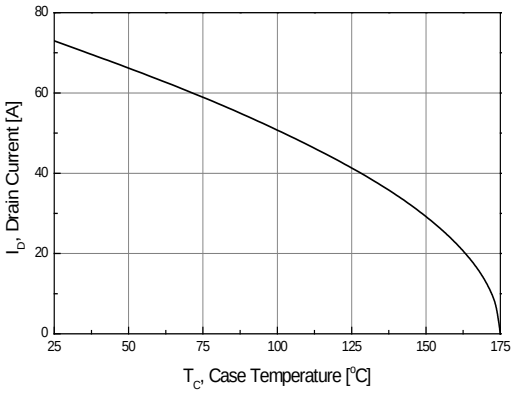

Figure 10. Maximum Drain Current vs Case Temperature

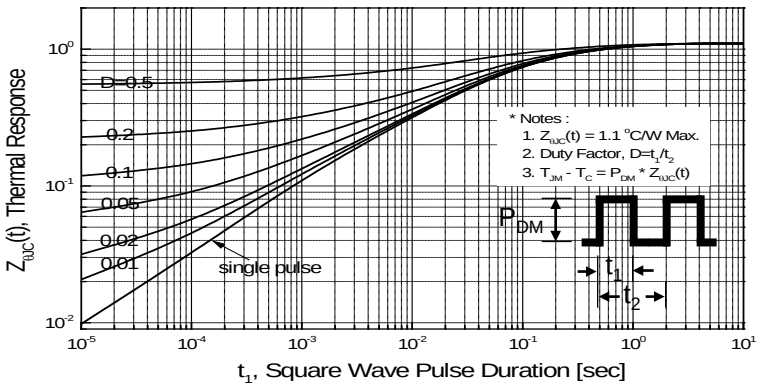

Figure 11. Transient Thermal Response Curve

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Fig 12. Gate Charge Test Circuit & Waveform

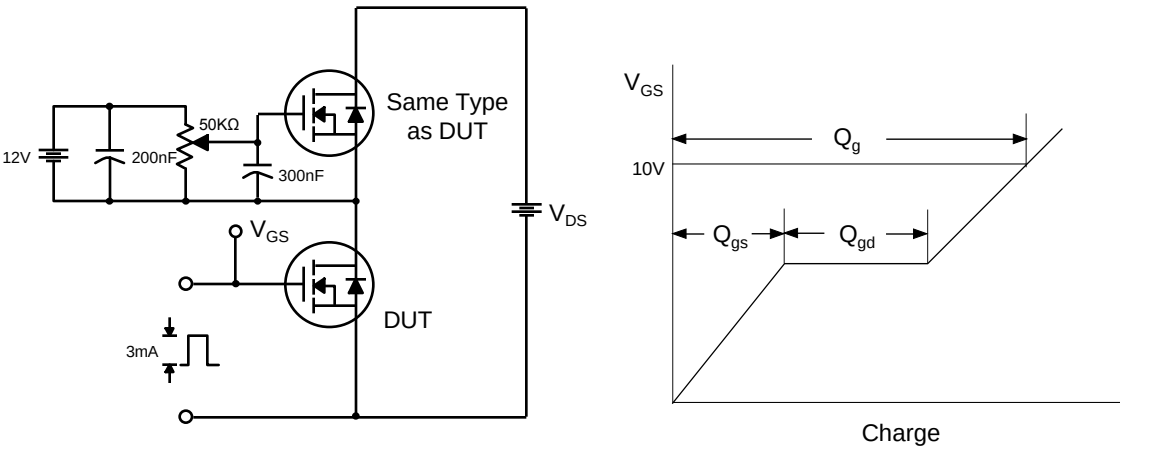

Fig 13. Resistive Switching Test Circuit & Waveforms

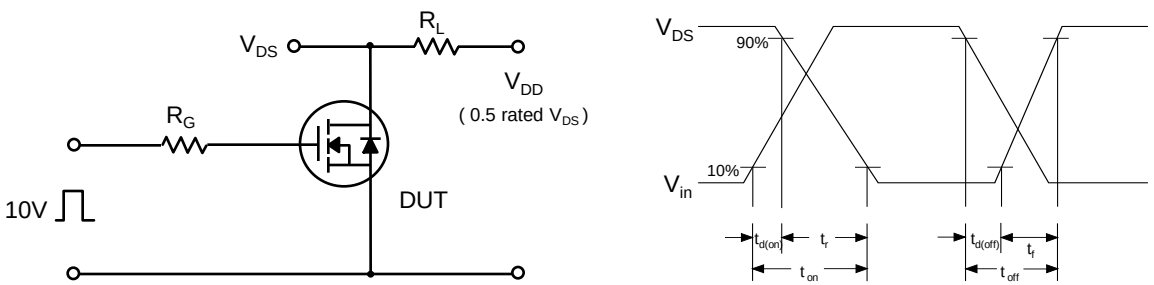

Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

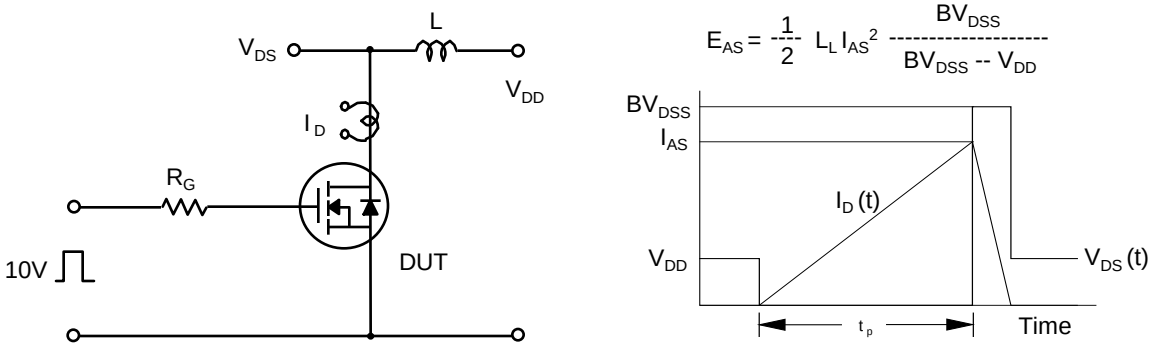

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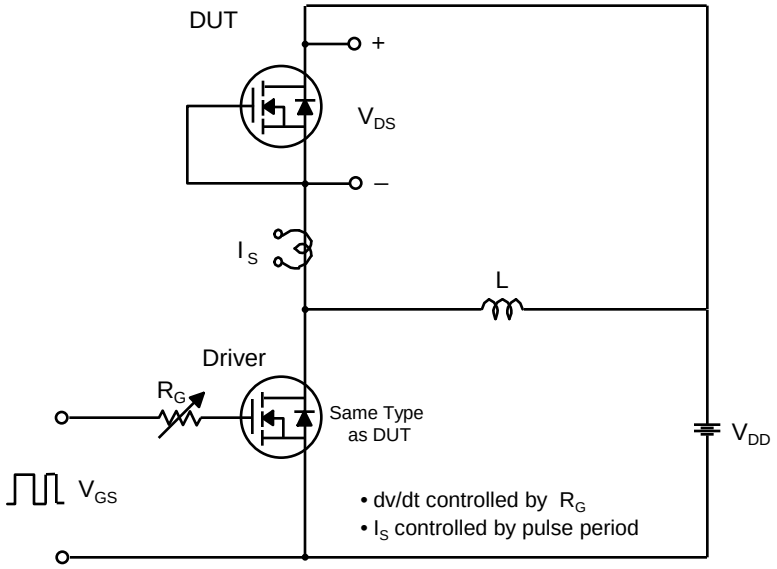
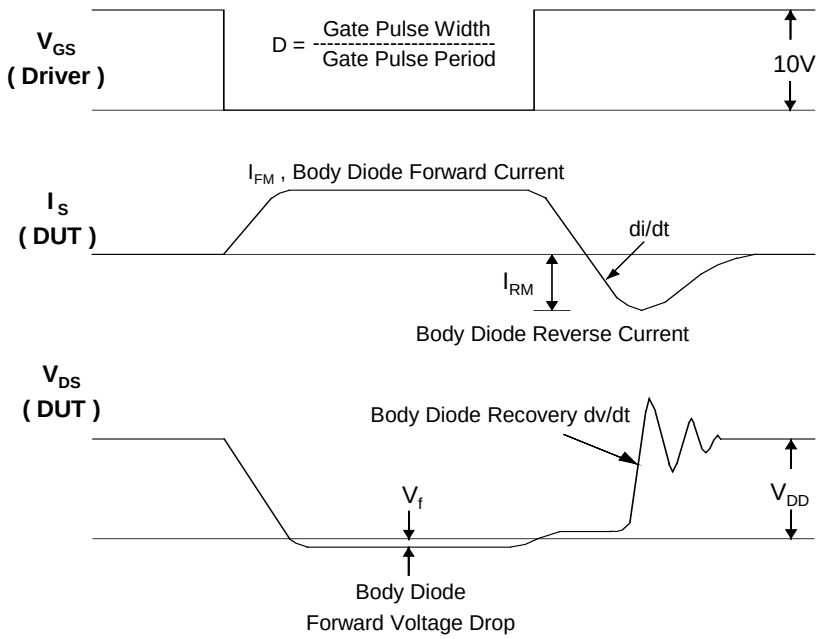
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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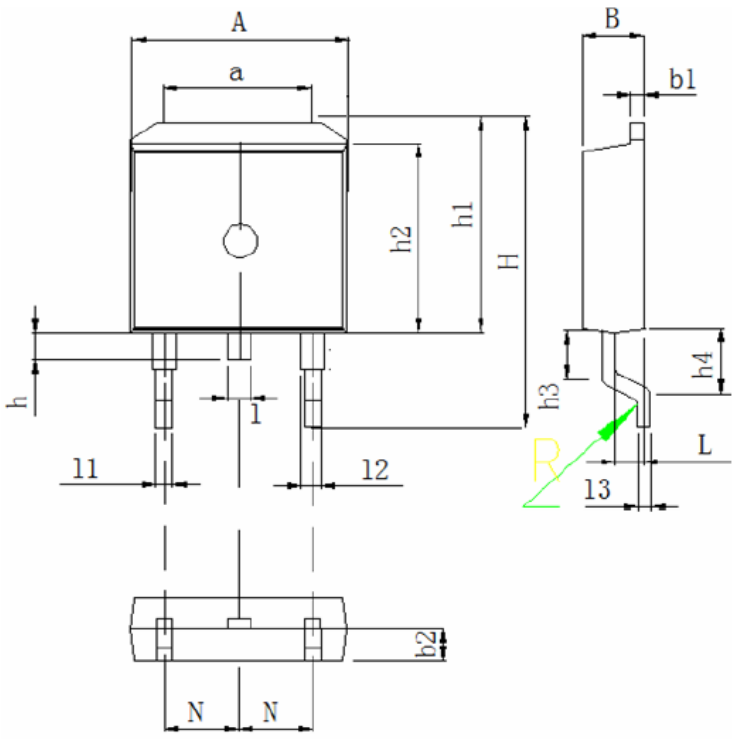
Package Dimension

D²-PAK
(TO-263)



DIM	MILLIMETERS
A	9.8±0.2
a	7.4±0.2
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	15.5±0.3
h	1.54±0.2
h1	10.5±0.2
h2	9.2±0.1
h3	1.54±0.2
h4	2.7±0.2
L	2.4±0.2
l	1.3±0.1
l1	0.8±0.1
l2	1.3±0.1
l3	0.5±0.1
N	2.45±0.05
R	0.5R±0.05

Unit :mm

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